

65W - 28V - 1GHz
GOLD METALIZED SILICON
DMOS RF FET

FEATURES

- METAL GATE
- EXTRA LOW C_{rss}
- BROAD BAND
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN

APPLICATIONS

- HF/VHF/UHF COMMUNICATIONS

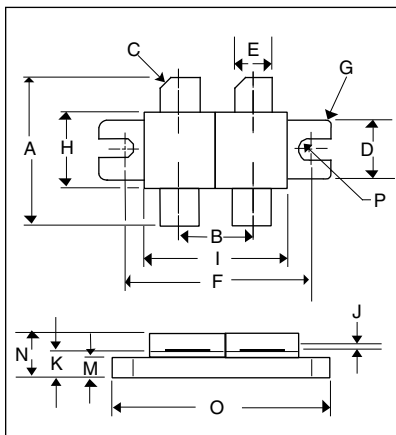
ABSOLUTE MAXIMUM RATINGS
($T_{CASE} = 25^{\circ}C$ unless otherwise stated)

P_D	Power Dissipation	207W
BV_{DSS}	Drain-source breakdown voltage	60V
V_{GSS}	Gate-source voltage	$\pm 20V$
I_D	Drain Current	16A
T_{stg}	Storage temperature	-65 to 150°C
T_j	Maximum operating junction temperature	200°C
$R_{\theta j-c}$	Thermal resistance junction-case	Max. .85°C/W

ELECTRICAL CHARACTERISTICS ($T_{CASE} = 25^{\circ}C$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
<u>PER SIDE</u>					
BV_{DSS}	Breakdown voltage, drain source $V_{GS}=0$ $I_D=100mA$	60	60	60	Vdc
I_{DSS}	Drain leakage current $V_{DS}=28V$ $V_{GS}=0$			2	mAdc
I_{GSS}	Gate leakage current $V_{GS}=20V$ $V_{DS}=0$			1	μ Adc
$V_{GS(th)}$	Gate threshold voltage $I_D=10mA$ $V_{DS}=V_{GS}$	1		5	Vdc
g_{fs}	Transconductance (300 μ s pulse) $V_{DS}=10V$ $I_D=1.4A$	1.4			Mhos
C_{iss}	Input capacitance $V_{DS}=0$ $V_{GS}=-0$ $f=1MHz$			96	pF
C_{oss}	Output capacitance $V_{DS}=0$ $V_{GS}=0$ $f=1MHz$			40	pF
C_{rss}	Reverse transfer capacitance $V_{DS}=0$ $V_{GS}=0$ $f=1MHz$			4.0	pF
<u>TOTAL DEVICE</u>					
G_{PS}	Common source power gain $P_O=65W$	10			dB
η	Drain efficiency $V_{DS}=28V$ $I_{DQ}=1.6A$	40			%
VSWR	Load mismatch tolerance $f=1GHz$	20:1			

DIMENSIONS



DM	Millimeter	TOL	Inches	TOL
A	15.24	.50	.750	.020
B	10.77	.13	.424	.005
C	45°	.05	45°	5°
D	9.78	.13	.385	.005
E	5.71	.13	.255	.005
F	27.94	.13	1.100	.005
G	1.52R	.13	.060R	.005
H	10.16	.13	.400	.005
I	22.22	MAX	.875	MAX
J	0.13	.02	.005	.001
K	2.16	.13	.107	.005
M	1.52	.13	.060	.005
N	5.08	.50	.200	.020
O	34.04	.13	1.340	.005
P	1.57R	.08	.062R	.003

HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area. THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.

U.S. PATENTS 5,121,176 & 5,179,032
GLOBAL PATENTS PENDING